Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	12294	first near interconnect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/11/01 17:15
<b>S2</b>	388774	(low adj dielectric adj constant) or low-k or ((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subn" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:28
<b>S</b> 3	1	10/721260	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:42
S4	722682	copper	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/11/01 17:35
S5	162754	((silicon adj nitride) or (SiN4 or SiNn or "SiN.sub4" or "SiN.subx" or "SiN.subn" or "SiN.sub.4" or "SiN.sub.x" or "SiN.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:35
S6	368831	((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.n"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:36
S7	2425	oxide near cap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:36
S8	457500	resist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:36
<b>S9</b>	3174751	via	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:36

S10	60407	fluorocarbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/11/01 17:36
S11	2907	C4F8 or "C.sub.4F.sub.8" or "C.sub. xF.sub.x" or "C.sub.nF.sub.n" or "C. sub.xF.sub.n" or "C.sub.nF.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:37
S14	758	C4F6 or "C.sub.4F.sub.6" or "C.sub. xF.sub.x" or "C.sub.nF.sub.n" or "C. sub.xF.sub.n" or "C.sub.nF.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:39
S15	741	C5F8 or "C.sub.5F.sub.8" or "C.sub. xF.sub.x" or "C.sub.nF.sub.n" or "C. sub.xF.sub.n" or "C.sub.nF.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:38
S16	588	C3F6 or "C.sub.3F.sub.6" or "C.sub. xF.sub.x" or "C.sub.nF.sub.n" or "C. sub.xF.sub.n" or "C.sub.nF.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:39
S17	3588	S11 or S14 or S15 or S16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:39
S18	376386	((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.sub.2" or "SiO.sub.2" or "SiO.sub.x" or "SiO.sub.x" or "SiO.sub.n")) or SOG or (spin adj on adj glass)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:46
S19   	3807219	contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:46
S20	7577030	(Argon or Ar\$3 or AR2 or ARx or ARn or ARsubx or ARsubn or "AR. subx" or "AR.subn" or "AR.sub.x" or "Ar.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/11/01 17:47
S21	2287183	(oxygen or O2 or Ox or On or Osubx or Osubn or "O.subx" or "O.sub.n")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:48

rr					Γ	
S22	1895	S17 and S20 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:48
S23	481	"60" adj mTorr	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/11/01 17:48
S24	184	(RF adj power) near "600"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:49
S25	447	(RF adj power) near "500"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:49
S26   	290	(RF adj power) near "400"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:49
S27	475	(RF adj power) near "300"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:49
S28	495	(RF adj power) near "200"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:50
S29	736	(RF adj power) near "100"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:50
S30	529	(RF adj power) near "50"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:50
S31	2553	S24 or S25 or S26 or S27 or S28 or S29 or S30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:53

S32	43	S22 and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:53
S33	66	S22 and S31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:53
S34	3	S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2006/11/01 18:18
S35	2	"6603206".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:10
S36	0	(via or hole or trench) near etch near (no near stop near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:12
S37	8525	(via or hole or trench) near etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:12
S38	6162154	S37 no (etch near stop near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/11/02 10:13
S39	6758	S37 not (etch near stop near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:13
S40	5755	S37 not (etch near stop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:13
S41	4654	S37 not (stop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:14

						·
S42 i	389191	(low adj dielectric adj constant) or low-k or ((silicon adj dioxide) or (SiO2 or SiOx or SiOn or "SiO.sub2" or "SiO.subx" or "SiO.subx" or "SiO.sub." or "SiO.sub." or "SiO.sub." or "SiO.sub." or "SiO.sub."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:14
S43	1883	S41 and S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:15
S44	78	S43 and (via.ti.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:15
S45	. 1	2004-356178	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:42
S46	2	2003-149057	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:42